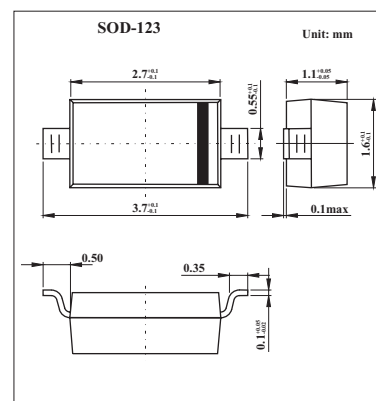


Silicon Schottky Barrier Diode

HSU88

■ Features

- Low capacitance. (C=0.8pF max)
- Low forward voltage.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Average rectified current	I_o	15	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1\text{ mA}$	350		420	mV
		$I_F = 10\text{ mA}$	500		580	
Reverse current	I_R	$V_R = 2\text{ V}$			0.2	$\mu\text{ A}$
		$V_R = 10\text{ V}$			10	
Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.8	pF
ESD-Capability (Note 1)		C = 200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geq 400\text{ nA}$ at $V_R = 2\text{ V}$

■ Marking

Marking	9
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